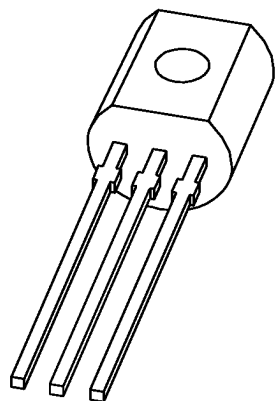


DATA SHEET



BC546; BC547; BC548 NPN general purpose transistors

Product specification

1997 Mar 04

Supersedes data of September 1994

File under Discrete Semiconductors, SC04

Philips
Semiconductors



PHILIPS

NPN general purpose transistors

BC546; BC547; BC548

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

APPLICATIONS

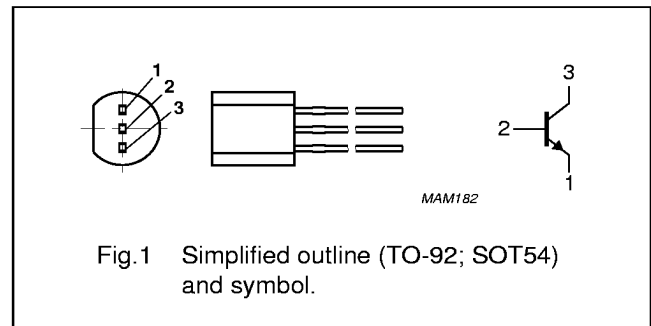
- General purpose switching and amplification.

DESCRIPTION

NPN transistor in a TO-92; SOT54 plastic package.
PNP complements: BC556, BC557 and BC558.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC546		–	80	V
	BC547		–	50	V
	BC548		–	30	V
V_{CEO}	collector-emitter voltage	open base			
	BC546		–	65	V
	BC547		–	45	V
	BC548		–	30	V
I_{CM}	peak collector current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	–	500	mW
h_{FE}	DC current gain	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$			
	BC546		110	450	
	BC547		110	800	
	BC548		110	800	
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	MHz

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BC546		–	80	V
	BC547		–	50	V
	BC548		–	30	V
V _{CEO}	collector-emitter voltage	open base			
	BC546		–	65	V
	BC547		–	45	V
	BC548		–	30	V
V _{EBO}	emitter-base voltage	open collector			
	BC546		–	6	V
	BC547		–	6	V
	BC548		–	5	V
I _C	collector current (DC)		–	100	mA
I _{CM}	peak collector current		–	200	mA
I _{BM}	peak base current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	500	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th-j-a}	thermal resistance from junction to ambient	note 1	0.25	K/mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN general purpose transistors

BC546; BC547; BC548

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

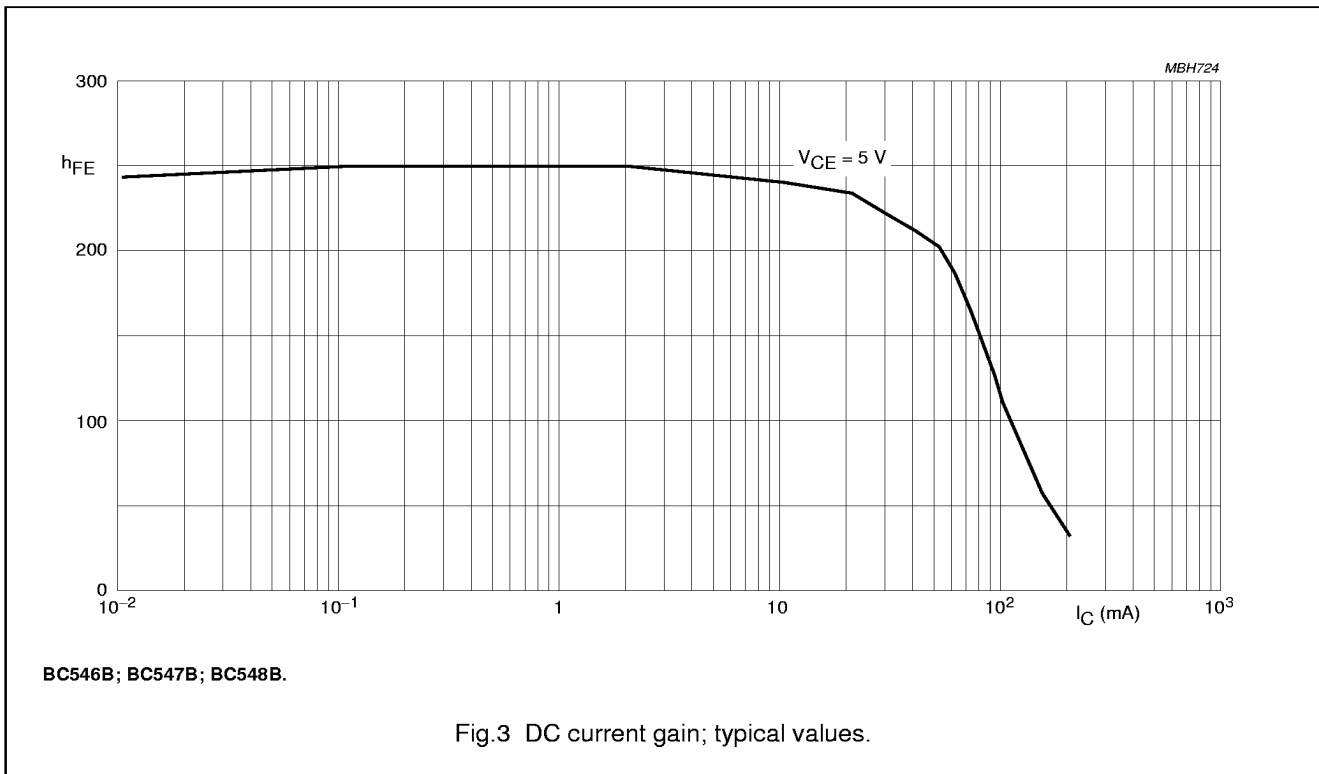
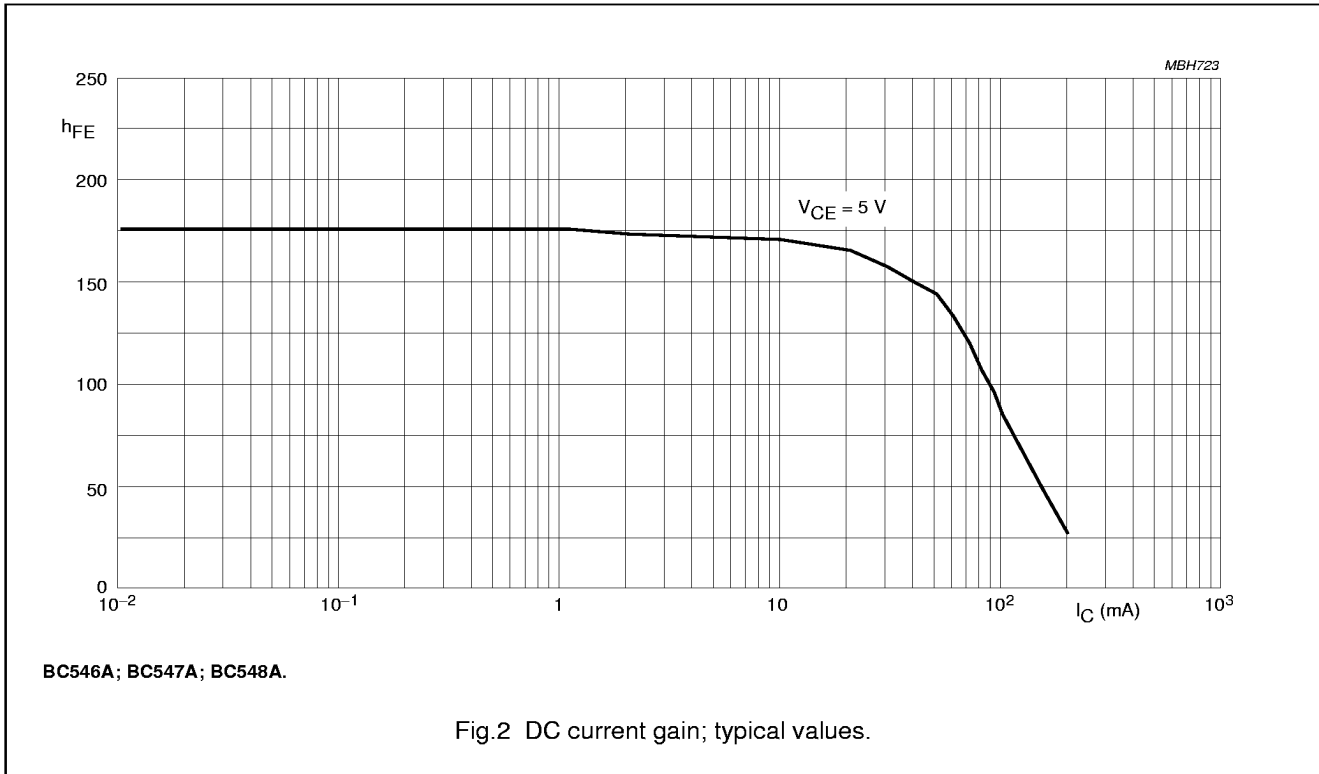
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	–	15	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ °C}$	–	–	5	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain BC546A; BC547A; BC548A BC546B; BC547B; BC548B BC547C; BC548C	$I_C = 10\text{ }\mu\text{A}; V_{CE} = 5\text{ V};$ see Figs 2, 3 and 4	–	90	–	
			–	150	–	
			–	270	–	
h_{FE}	DC current gain BC546A; BC547A; BC548A BC546B; BC547B; BC548B BC547C; BC548C BC547; BC548 BC546	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V};$ see Figs 2, 3 and 4	110	180	220	
			200	290	450	
			420	520	800	
			110	–	800	
			110	–	450	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	90	250	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	–	200	600	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA};$ note 1	–	700	–	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA};$ note 1	–	900	–	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V};$ note 2	580	660	700	mV
		$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	–	–	770	mV
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	1.5	–	pF
C_e	emitter capacitance	$I_C = I_c = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	11	–	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V};$ $R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	–	2	10	dB

Notes

- V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.
- V_{BE} decreases by about 2 mV/K with increasing temperature.

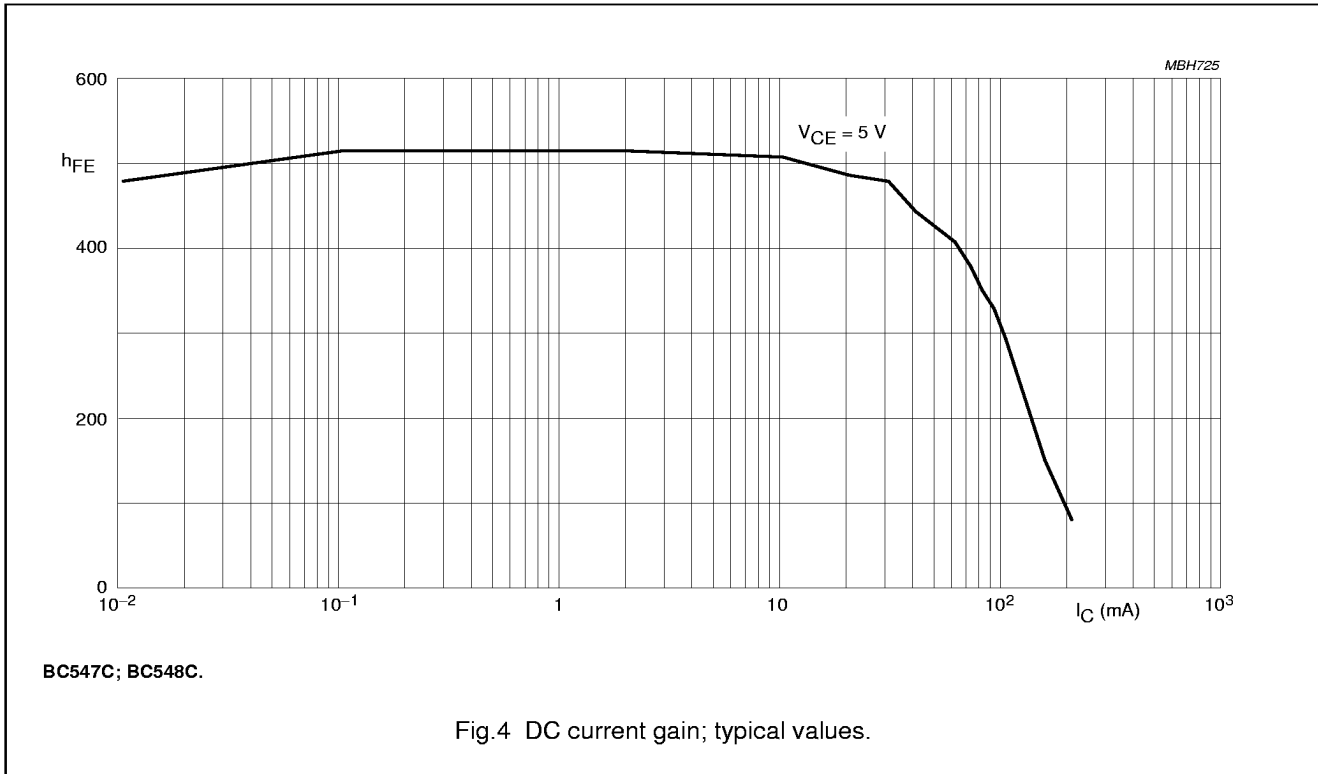
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BC546; BC547; BC548



NPN general purpose transistors

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NPN general purpose transistors

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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

